# **High Voltage Transistors**

#### **NPN Silicon**

#### **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage MMBTA42, SMMBTA42 MMBTA43	V <sub>CEO</sub>	300 200	Vdc
Collector - Base Voltage MMBTA42, SMMBTA42 MMBTA43	V <sub>CBO</sub>	300 200	Vdc
Emitter – Base Voltage MMBTA42, SMMBTA42 MMBTA43	V <sub>EBO</sub>	6.0 6.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	500	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

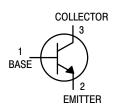
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



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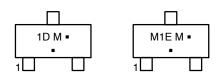
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SOT-23 (TO-236) CASE 318 STYLE 6

#### **MARKING DIAGRAMS**



1D = MMBTA42LT, SMMBTA42L

M1E = MMBTA43LT M = Date Code\* ■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				1	•
Collector – Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	MMBTA42, SMMBTA42 MMBTA43	V <sub>(BR)CEO</sub>	300 200	- -	Vdc
Collector – Base Breakdown Voltage (I <sub>C</sub> = 100 μAdc, I <sub>E</sub> = 0)	MMBTA42, SMMBTA42 MMBTA43	V <sub>(BR)CBO</sub>	300 200	- -	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 100 \mu Adc, I_C = 0$ )		V <sub>(BR)EBO</sub>	6.0	-	Vdc
Collector Cutoff Current $(V_{CB} = 200 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 160 \text{ Vdc}, I_E = 0)$	MMBTA42, SMMBTA42 MMBTA43	Ісво	- -	0.1 0.1	μAdc
Emitter Cutoff Current $(V_{EB} = 6.0 \text{ Vdc}, I_C = 0)$ $(V_{EB} = 4.0 \text{ Vdc}, I_C = 0)$	MMBTA42, SMMBTA42 MMBTA43	I <sub>EBO</sub>	- -	0.1 0.1	μAdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ )	Both Types Both Types	h <sub>FE</sub>	25 40	- -	-
$(I_C = 30 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$	MMBTA42, SMMBTA42 MMBTA43		40 40	_ _	
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 20 mAdc, I <sub>B</sub> = 2.0 mAdc)	MMBTA42, SMMBTA42 MMBTA43	V <sub>CE(sat)</sub>	- -	0.5 0.5	Vdc
Base–Emitter Saturation Voltage ( $I_C = 20 \text{ mAdc}$ , $I_B = 2.0 \text{ mAdc}$ )		V <sub>BE(sat)</sub>	-	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				•	
Current – Gain – Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)		f <sub>T</sub>	50	_	MHz
Collector-Base Capacitance (V <sub>CB</sub> = 20 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	MMBTA42, SMMBTA42 MMBTA43	C <sub>cb</sub>	- -	3.0 4.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width  $\leq 300~\mu$ s, Duty Cycle  $\leq 2.0\%$ .

#### **TYPICAL CHARACTERISTICS**

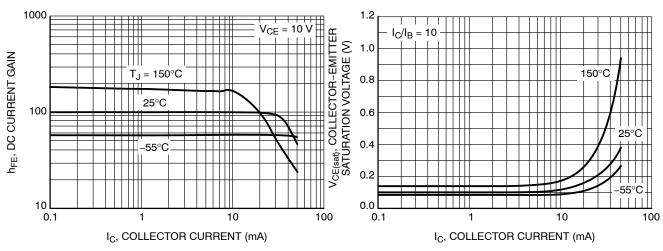


Figure 1. DC Current Gain

Figure 2. Collector–Emitter Saturation Voltage vs. Collector Current

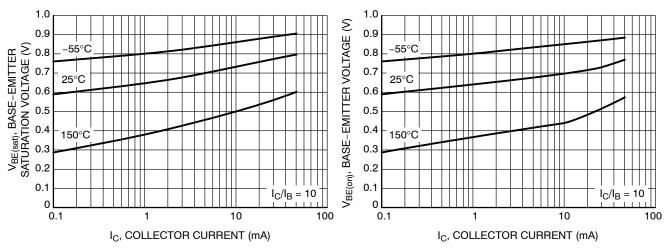


Figure 3. Base-Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base-Emitter On Voltage vs. Collector Current

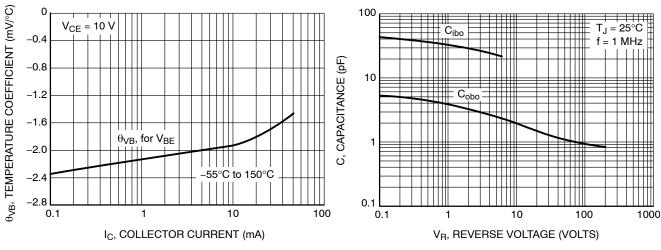


Figure 5. Base-Emitter Temperature Coefficient

Figure 6. Capacitance

#### **TYPICAL CHARACTERISTICS**

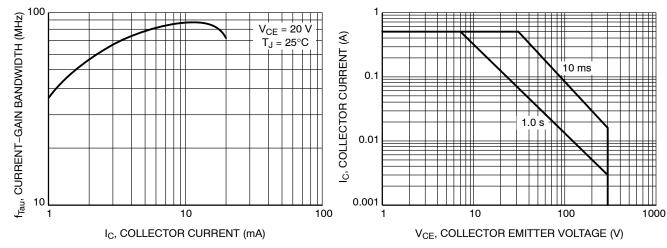


Figure 7. Current-Gain — Bandwidth Product

Figure 8. Safe Operating Area

#### **ORDERING INFORMATION**

Device Order Number	Package Type	Shipping <sup>†</sup>
MMBTA42LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA42LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA42LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBTA42LT3G	STA42LT3G SOT-23 (Pb-Free) 10,000 / Ta	
MMBTA43LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

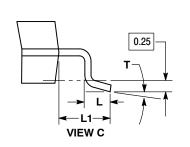


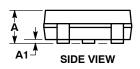
SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

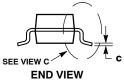
**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

**TOP VIEW** 







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
<ol><li>ANODE</li></ol>	<ol><li>SOURCE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. DRAIN	2. GATE
<ol><li>CATHODE</li></ol>	3. GATE	<ol><li>CATHODE-ANODE</li></ol>	<ol><li>ANODE</li></ol>	3. GATE	<ol><li>ANODE</li></ol>

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>ANODE</li></ol>
<ol><li>ANODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>CATHODE-ANOD</li></ol>	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
<ol><li>SOURCE</li></ol>	<ol><li>OUTPUT</li></ol>	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	<ol><li>NO CONNECTION</li></ol>

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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2N2369ADCSM 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E

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